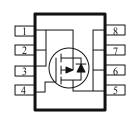
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low r_{DS(on)} assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- $\begin{array}{ll} \bullet & \quad \text{Low } r_{DS(on)} \, \text{Provides Higher Efficiency and} \\ \text{Extends Battery Life} \\ \end{array}$
- Miniature SO-8 Surface Mount Package Sar Board Space
- High power and current handling capability

PRODUCT SUMMARY				
V _{DS} (V)	$r_{\mathrm{DS}(\mathrm{on})} m(\Omega)$	$I_{D}(A)$		
	$13 @ V_{GS} = -4.5V$	-11.5		
-20	$19 @ V_{GS} = -2.5V$	-10		
	$35 @ V_{GS} = -1.8V$	-7.7		





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage			-20	V		
Gate-Source Voltage	V_{GS}	±12	V			
C . D . C . d	$T_A=25^{\circ}C$	<u>.</u> Т_	-13.4			
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1D	-8.4	A		
Pulsed Drain Current ^b	I_{DM}	±50				
Continuous Source Current (Diode Conduction) ^a		I_S	-2.1	A		
D D: a	$T_A=25^{\circ}C$	D	3.1	W		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	rD	2.0	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W	
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	40	°C/W	

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Crymbal	Took Conditions	Limits			Unit
r ar ameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.7			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zero Gate Voltage Drain Current	1055	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -4.5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			A
		$V_{GS} = -4.5 \text{ V}, I_D = -11.5 \text{ A}$			11.5	
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = -2.5 \text{ V}, I_D = -10.4 \text{ A}$			19	mΩ
		$V_{GS} = -1.8 \text{ V}, I_D = -7.7 \text{ A}$			35	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -11.5 \text{ A}$		70		S
Diode Forward Voltage	V_{SD}	$I_S = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.6		V
Dynamic ^b						
Total Gate Charge	Q_{g}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		33.4		
Gate-Source Charge	Q_{gs}	$I_{DS} = -10 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -11.5 \text{ A}$		5.9		nC
Gate-Drain Charge	Q_{gd}			8.1		
Turn-On Delay Time	t _{d(on)}			20		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_L = 6 \Omega, I_D = -1 \text{ A},$		23		nS
Turn-Off Delay Time	$t_{d(off)}$	VGEN = -4.5 V		289		113
Fall-Time	t_{f}			134		

Notes

a. Pulse test: $PW \le 300us duty cycle \le 2\%$.

b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (P-Channel)

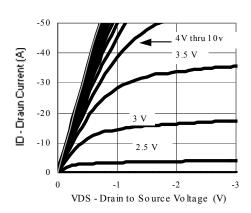


Figure 1. On-Region Characteristics

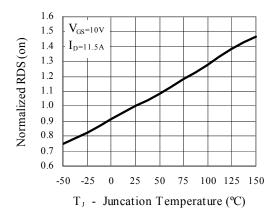
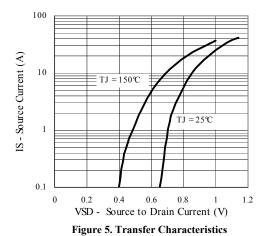


Figure 3. On-Resistance Variation with Temperature



 $\begin{array}{c} 0.03 \\ 0.026 \\ \hline \\ 0.018 \\ 0.014 \\ \hline \\ 0.014 \\ \hline \\ 0.014 \\ \hline \\ 0.014 \\ \hline \\ 0.016 \\ \hline \\ 0.014 \\ \hline \\ 0.016 \\ \hline \\ 0.014 \\ \hline \\ 0.016 \\$

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

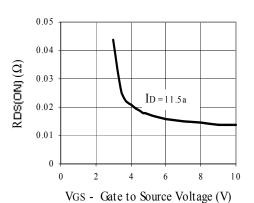


Figure 4. On-Resistance with Gate to Source Voltage

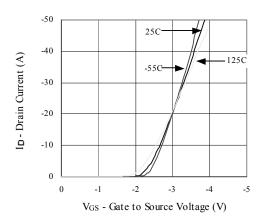


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (P-Channel)

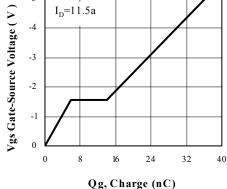


Figure 7. Gate Charge Characteristics

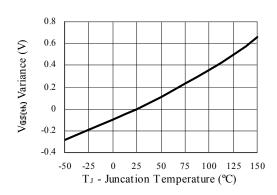


Figure 9. Maximum Safe Operating Area

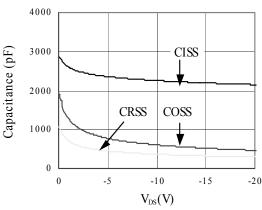


Figure 8. Capacitance Characteristics

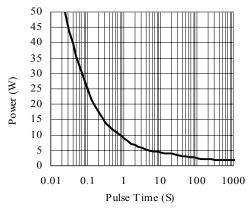


Figure 10. Single Pulse Maximum Power Dissipation

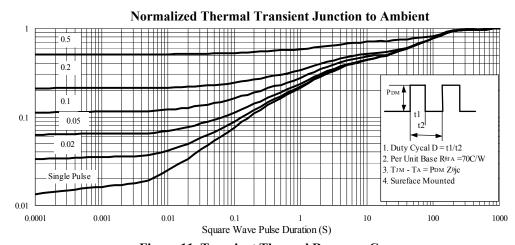
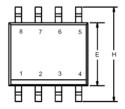


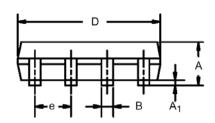
Figure 11. Transient Thermal Response Curve

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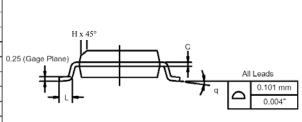
Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	



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